CD4066B CMOS Quad Bilateral Switch

1 Features

- 15-V Digital or ±7.5-V Peak-to-Peak Switching
- 125-Ω Typical On-State Resistance for 15-V Operation
- Switch On-State Resistance Matched to Within 5 Ω Over 15-V Signal-Input Range
- On-State Resistance Flat Over Full Peak-to-Peak Signal Range
- High ON/OFF Output-Voltage Ratio: 80 dB Typical at f_{is} = 10 kHz, R_L = 1 kΩ
- High Degree of Linearity: <0.5% Distortion Typical at f_{is} = 1 kHz, V_{is} = 5 V_{p-p} $V_{DD} - V_{SS} \geq 10$ V, R_L = 10 kΩ
- Extremely Low Off-State Switch Leakage, Resulting in Very Low Offset Current and High Effective Off-State Resistance: 10 pA Typical at $V_{DD} - V_{SS}$ = 10 V, T_A = 25°C
- Extremely High Control Input Impedance (Control Circuit Isolated From Signal Circuit): 10^{12} Ω Typical
- Low Crosstalk Between Switches: –50 dB Typical at f_{is} = 8 MHz, R_L = 1 kΩ
- Matched Control-Input to Signal-Output Capacitance: Reduces Output Signal Transients
- Frequency Response, Switch On = 40 MHz Typical
- 100% Tested for Quiescent Current at 20 V
- 5-V, 10-V, and 15-V Parametric Ratings

2 Applications

- Analog Signal Switching/Multiplexing: Signal Gating, Modulators, Squelch Controls, Demodulators, Choppers, Commutating Switches
- Digital Signal Switching/Multiplexing
- Transmission-Gate Logic Implementation
- Analog-to-Digital and Digital-to-Analog Conversions
- Digital Control of Frequency, Impedance, Phase, and Analog-Signal Gain

3 Description

The CD4066B device is a quad bilateral switch intended for the transmission or multiplexing of analog or digital signals. It is pin-for-pin compatible with the CD4016B device, but exhibits a much lower on-state resistance. In addition, the on-state resistance is relatively constant over the full signal-input range.

The CD4066B device consists of four bilateral switches, each with independent controls. Both the p and the n devices in a given switch are biased on or off simultaneously by the control signal. As shown in Figure 17, the well of the n-channel device on each switch is tied to either the input (when the switch is on) or to V_{SS} (when the switch is off). This configuration eliminates the variation of the switch-transistor threshold voltage with input signal and, thus, keeps the on-state resistance low over the full operating-signal range.

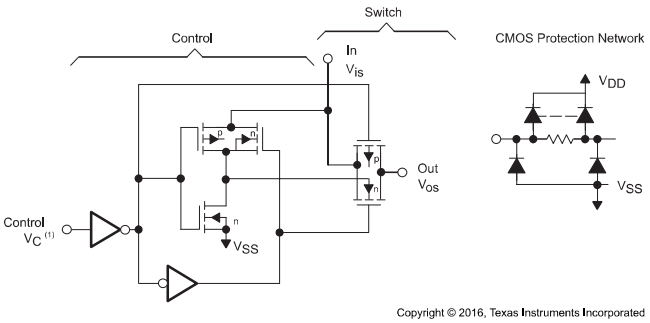
The advantages over single-channel switches include peak input-signal voltage swings equal to the full supply voltage and more constant on-state impedance over the input-signal range. However, for sample-and-hold applications, the CD4016B device is recommended.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
CD4066B	PDIP (14)	19.30 mm × 6.35 mm
	CDIP (14)	19.50 mm × 6.92 mm
	SOIC (14)	8.65 mm × 3.91 mm
	SOP (14)	10.30 mm × 5.30 mm
	TSSOP (14)	5.00 mm × 4.40 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

Bidirectional Signal Transmission Via Digital Control Logic



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision F (March 2017) to Revision G — **Page**

- Changed From: V_{SS} To: Hi-Z in the SIG OUT/IN column of Table 1 ... 14

Changes from Revision E (September 2016) to Revision F — **Page**

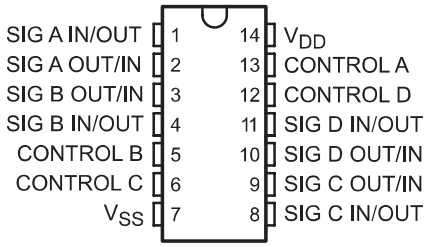
- Corrected the r_{on} V_{DD} = 10 V values in the *Electrical Characteristics* table. ... 7
- Corrected the y axis scale in Figure 6 ... 9

Changes from Revision D (September 2003) to Revision E — **Page**

- Added *ESD Ratings* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section ... 1
- Deleted *Ordering Information* table, see POA at the end of the data sheet ... 1
- Changed values in the *Thermal Information* table to align with JEDEC standards ... 4

5 Pin Configuration and Functions

N, J, D, NS, or PW Packages
14-Pin PDIP, CDIP, SOIC, SO, or TSSOP
Top View



Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	SIG A IN/OUT	I/O	Input/Output for Switch A
2	SIG A OUT/IN	I/O	Output/Input for Switch A
3	SIG B OUT/IN	I/O	Output/Input for Switch B
4	SIG B IN/OUT	I/O	Input/Output for Switch B
5	CONTROL B	I	Control pin for Switch B
6	CONTROL C	I	Control pin for Switch C
7	V_{SS}	—	Low Voltage Power Pin
8	SIG C IN/OUT	I/O	Input/Output for Switch C
9	SIG C OUT/IN	I/O	Output/Input for Switch C
10	SIG D OUT/IN	I/O	Output/Input for Switch D
11	SIG D IN/OUT	I/O	Input/Output for Switch D
12	CONTROL D	I	Control Pin for D
13	CONTROL A	I	Control Pin for A
14	V_{DD}	—	Power Pin

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{DD}	DC supply-voltage	Voltages referenced to V_{SS} pin	–0.5	20	V
V_{is}	Input voltage	All inputs	–0.5	V_{DD} + 0.5	V
I_{IN}	DC input current	Any one input		±10	mA
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±500	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	±1500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{DD}	Supply voltage	3	18	V
T_A	Operating free-air temperature	–55	125	°C

6.4 Thermal Information

THERMAL METRIC(1)		CD4066B				UNIT
		N (PDIP)	D (SOIC)	NS (SO)	PW (TSSOP)	
		14 PINS	14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	53.7	89.5	88.2	119.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	41.0	49.7	46.1	48.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	33.6	43.8	47.0	61.2	°C/W
ψ_{JT}	Junction-to-top characterization parameter	25.8	17.4	16.3	5.5	°C/W
ψ_{JB}	Junction-to-board characterization parameter	33.5	43.5	46.6	60.6	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{os}	Switch output voltage	V_{DD} = 5 V V_{is} = 0 V				0.4	V
		V_{DD} = 5 V V_{is} = 5 V		4.6			V
		V_{DD} = 10 V V_{is} = 0 V				0.5	V
		V_{DD} = 10 V V_{is} = 10 V		9.5			V
		V_{DD} = 15 V V_{is} = 0 V				1.5	V
		V_{DD} = 15 V V_{is} = 15 V		13.5			V
Δr_{on}	On-state resistance difference between any two switches	R_L = 10 kΩ, V_C = V_{DD}	V_{DD} = 5 V		15		Ω
			V_{DD} = 10 V		10		
			V_{DD} = 15 V		5		
THD	Total harmonic distortion	V_C = V_{DD} = 5 V, V_{SS} = –5 V, $V_{is(p-p)}$ = 5 V (sine wave centered on 0 V), R_L = 10 kΩ, f_{is} = 1-kHz sine wave			0.4%		
	–3-dB cutoff frequency (switch on)	V_C = V_{DD} = 5 V, V_{SS} = –5 V, $V_{is(p-p)}$ = 5 V (sine wave centered on 0 V), R_L = 1 kΩ			40		MHz
	–50-dB feedthrough frequency (switch off)	V_C = V_{SS} = –5 V, $V_{is(p-p)}$ = 5 V (sine wave centered on 0 V), R_L = 1 kΩ			1		MHz
	–50-dB crosstalk frequency	V_C(A) = V_{DD} = 5 V, V_C(B) = V_{SS} = –5 V, V_{is}(A) = 5 V_{p-p}, 50-Ω source, R_L = 1 kΩ			8		MHz
C_{is}	Input capacitance	V_{DD} = 5 V, V_C = V_{SS} = –5 V			8		pF
C_{os}	Output capacitance	V_{DD} = 5 V, V_C = V_{SS} = –5 V			8		pF
C_{ios}	Feedthrough	V_{DD} = 5 V, V_C = V_{SS} = –5 V			0.5		pF
V_{IHC}	Control input, high voltage	See Figure 7	V_{DD} = 5 V	3.5			V
			V_{DD} = 10 V	7			
			V_{DD} = 15 V	11			
	Crosstalk (control input to signal output)	V_C = 10 V (square wave), t_r, t_f = 20 ns, R_L = 10 kΩ V_{DD} = 10 V			50		mV
	Turnon and turnoff propagation delay	V_{IN} = V_{DD}, t_r, t_f = 20 ns, C_L = 50 pF, R_L = 1 kΩ	V_{DD} = 5 V		35	70	ns
			V_{DD} = 10 V		20	40	
			V_{DD} = 15 V		15	30	
	Maximum control input repetition rate	V_{is} = V_{DD}, V_{SS} = GND, R_L = 1 kΩ to GND, C_L = 50 pF, V_C = 10 V (square wave centered on 5 V), t_r, t_f = 20 ns, V_{os} = 1/2 V_{os} at 1 kHz	V_{DD} = 5 V		6		MHz
			V_{DD} = 10 V		9		
			V_{DD} = 15 V		9.5		
C_I	Input capacitance				5	7.5	pF

Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
I_{is}	Switch input current	V_{DD} = 5 V V_{is} = 0 V	T_A = –55°C			0.64	mA
			T_A = –40°C			0.61	
			T_A = 25°C		0.51		
			T_A = 85°C			0.42	
			T_A = 125°C			0.36	
		V_{DD} = 5 V V_{is} = 5 V	T_A = –55°C			–0.64	mA
			T_A = –40°C			–0.61	
			T_A = 25°C		–0.51		
			T_A = 85°C			–0.42	
			T_A = 125°C			–0.36	
		V_{DD} = 10 V V_{is} = 0 V	T_A = –55°C			1.6	mA
			T_A = –40°C			1.5	
			T_A = 25°C		1.3		
			T_A = 85°C			1.1	
			T_A = 125°C			0.9	
		V_{DD} = 10 V V_{is} = 10 V	T_A = –55°C			–1.6	mA
			T_A = –40°C			–1.5	
			T_A = 25°C		–1.3		
			T_A = 85°C			–1.1	
			T_A = 125°C			–0.9	
		V_{DD} = 15 V V_{is} = 0 V	T_A = –55°C			4.2	mA
			T_A = –40°C			4	
			T_A = 25°C		3.4		
			T_A = 85°C			2.8	
			T_A = 125°C			2.4	
		V_{DD} = 15 V V_{is} = 15 V	T_A = –55°C			–4.2	mA
			T_A = –40°C			–4	
			T_A = 25°C		–3.4		
			T_A = 85°C			–2.8	
			T_A = 125°C			–2.4	

Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
I_{DD}	Quiescent device current	V_{IN} = 0 to 5 V, V_{DD} = 5 V	T_A = –55°C				0.25	µA
			T_A = –40°C				0.25	
			T_A = 25°C			0.01	0.25	
			T_A = 85°C				7.5	
			T_A = 125°C				7.5	
		V_{IN} = 0 to 10 V, V_{DD} = 10 V	T_A = –55°C				0.5	µA
			T_A = –40°C				0.5	
			T_A = 25°C			0.01	0.5	
			T_A = 85°C				15	
			T_A = 125°C				15	
		V_{IN} = 0 to 15 V, V_{DD} = 15 V	T_A = –55°C				1	µA
			T_A = –40°C				1	
			T_A = 25°C			0.01	1	
			T_A = 85°C				30	
			T_A = 125°C				30	
		V_{IN} = 0 to 20 V, V_{DD} = 20 V	T_A = –55°C				5	µA
			T_A = –40°C				5	
			T_A = 25°C			0.02	5	
			T_A = 85°C				150	
			T_A = 125°C				150	
r_{on}	On-state resistance (max)	to $\frac{(V_{DD} - V_{SS})}{2}$, $V_C = V_{DD}$, R_L = 10 kΩ returned $V_{is} = V_{SS}$ to V_{DD}	V_{DD} = 5 V	T_A = –55°C			800	Ω
				T_A = –40°C			850	
				T_A = 25°C		470	1050	
				T_A = 85°C			1200	
				T_A = 125°C			1300	
			V_{DD} = 10 V	T_A = –55°C			310	
				T_A = –40°C			330	
				T_A = 25°C		180	400	
				T_A = 85°C			500	
				T_A = 125°C			500	
			V_{DD} = 15 V	T_A = –55°C			200	
				T_A = –40°C			210	
				T_A = 25°C		125	240	
				T_A = 85°C			300	
				T_A = 125°C			320	

Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
V_{ILC}	Control input, low voltage (max)	$\|I_{is}\|$ < 10 µA, $V_{is} = V_{SS}$, $V_{OS} = V_{DD}$, and $V_{is} = V_{DD}$, $V_{OS} = V_{SS}$	V_{DD} = 5 V	T_A = –55°C		1		V
				T_A = –40°C		1		
				T_A = 25°C		1		
				T_A = 85°C		1		
				T_A = 125°C		1		
			V_{DD} = 10 V	T_A = –55°C		2		
				T_A = –40°C		2		
				T_A = 25°C		2		
				T_A = 85°C		2		
				T_A = 125°C		2		
			V_{DD} = 15 V	T_A = –55°C		2		
				T_A = –40°C		2		
				T_A = 25°C		2		
				T_A = 85°C		2		
				T_A = 125°C		2		
I_{IN}	Input current (max)	$V_{is} \le V_{DD}$, $V_{DD} - V_{SS}$ = 18 V, $V_{CC} \le V_{DD} - V_{SS}$ V_{DD} = 18 V	T_A = –55°C				±0.1	µA
			T_A = –40°C				±0.1	
			T_A = 25°C			$\pm 10^{-5}$	±0.1	
			T_A = 85°C				±1	
			T_A = 125°C				±1	

6.6 Switching Characteristics

T_A = 25°C

PARAMETER	FROM	TO	TEST CONDITIONS	V_{CC}	MIN	TYP	MAX	UNIT
t_{pd}	Signal input	Signal output	$V_{IN} = V_{DD}$, t_r, t_f = 20 ns, C_L = 50 pF, R_L = 1 kΩ	5 V		20	40	ns
				10 V		10	20	
				15 V		7	15	
t_{plh}	Signal input	Signal output	$V_{IN} = V_{DD}$, t_r, t_f = 20 ns, C_L = 50 pF, R_L = 1 kΩ	5 V		35	70	ns
				10 V		20	40	
				15 V		15	30	
t_{phl}	Signal input	Signal output	$V_{IN} = V_{DD}$, t_r, t_f = 20 ns, C_L = 50 pF, R_L = 1 kΩ	5 V		35	70	ns
				10 V		20	40	
				15 V		15	30	

6.7 Typical Characteristics

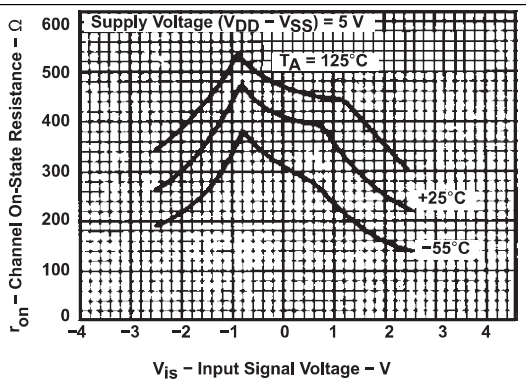


Figure 1. Typical ON-State Resistance vs Input Signal Voltage (All Types)

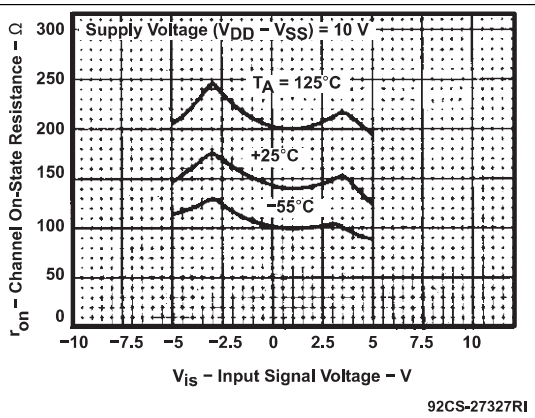


Figure 2. Typical ON-State Resistance vs Input Signal Voltage (All Types)

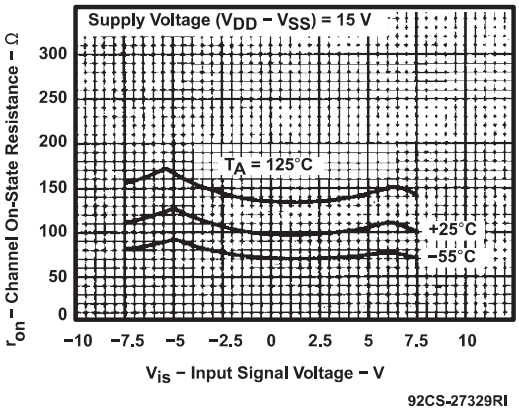


Figure 3. Typical ON-State Resistance vs Input Signal Voltage (All Types)

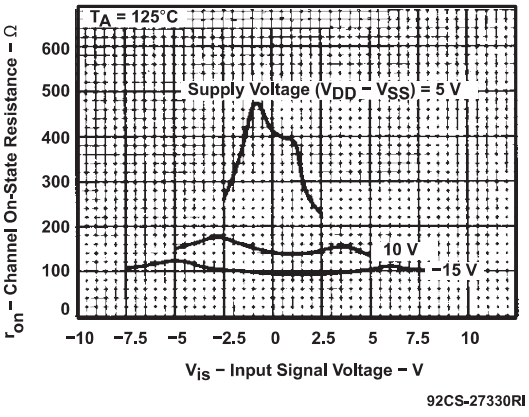


Figure 4. Typical ON-State Resistance vs Input Signal Voltage (All Types)

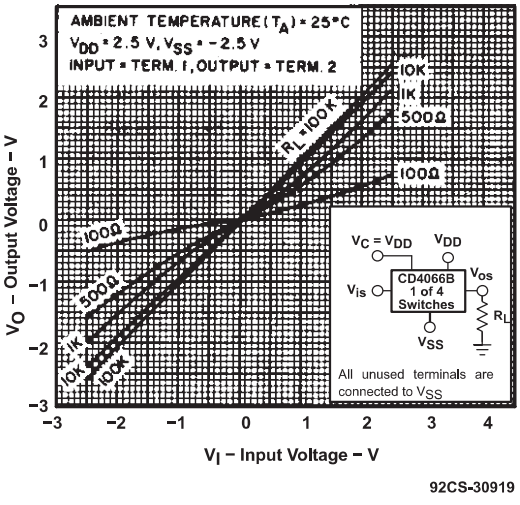


Figure 5. Typical ON Characteristics for 1 of 4 Channels

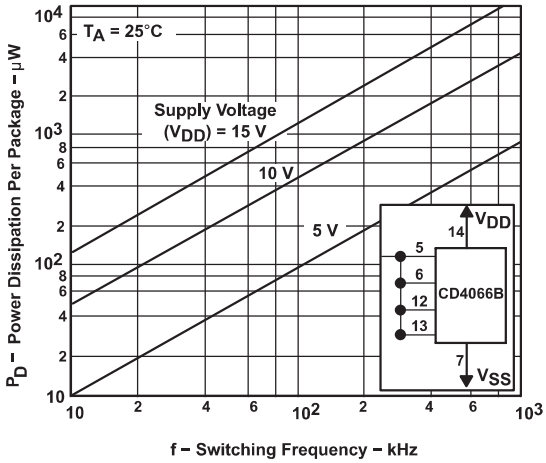


Figure 6. Power Dissipation per Package vs Switching Frequency

7 Parameter Measurement Information

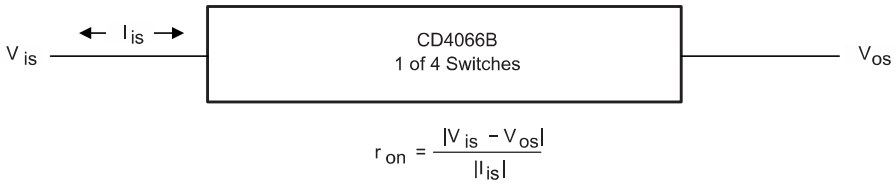


Figure 7. Determination of r_{on} as a Test Condition for Control-Input High-Voltage (V_{IHC}) Specification

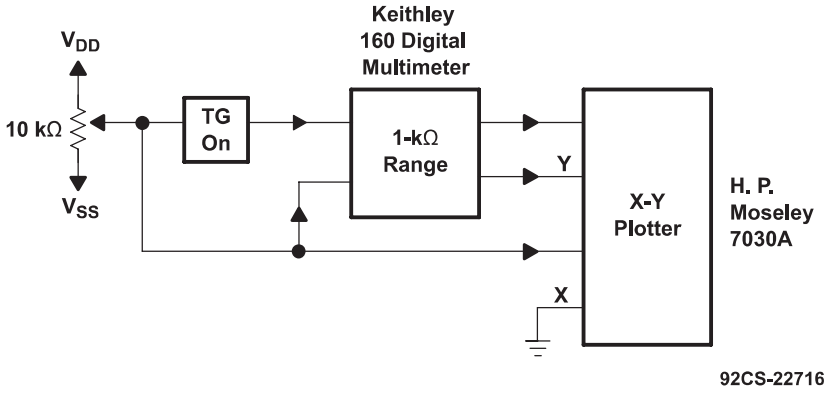
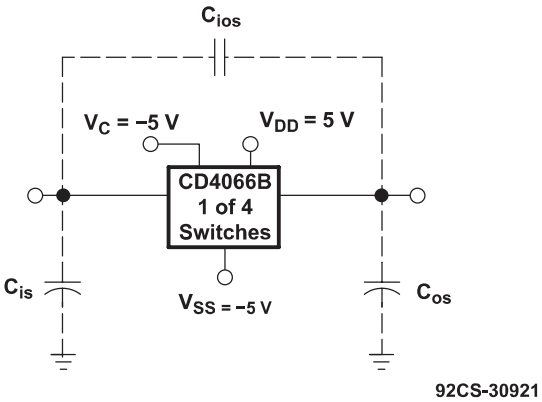


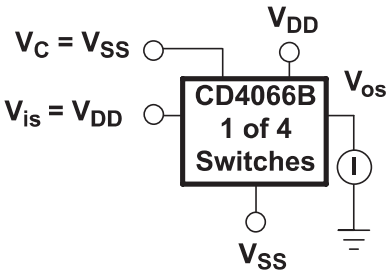
Figure 8. Channel On-State Resistance Measurement Circuit



Measured on Boonton capacitance bridge, model 75a (1 MHz);
test-fixture capacitance nulled out.

Figure 9. Typical On Characteristics for One of Four Channels

Parameter Measurement Information (continued)



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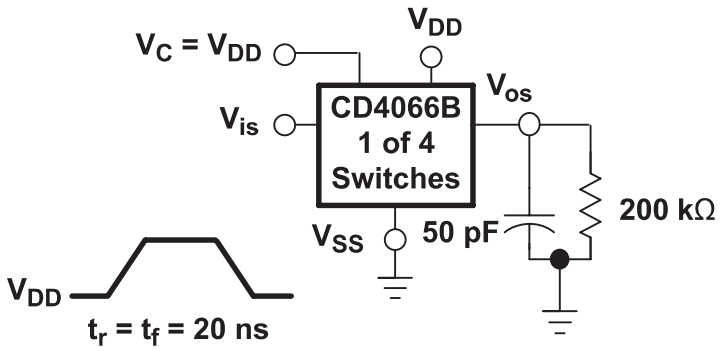
All unused terminals are connected to V_{SS}.

Figure 10. Off-Switch Input or Output Leakage



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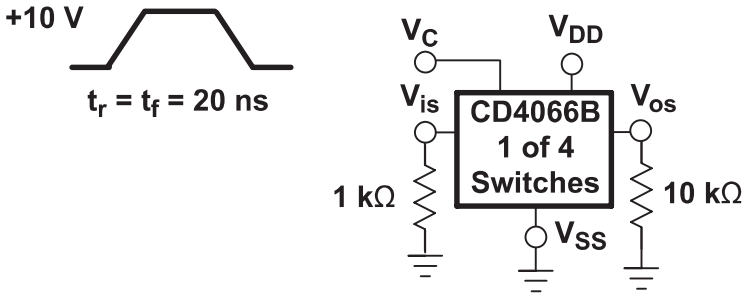
All unused terminals are connected to V_{SS}.

Figure 11. Propagation Delay Time Signal Input (V_{is}) to Signal Output (V_{os})



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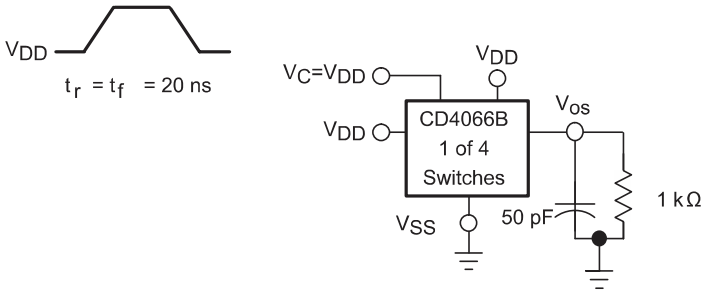
All unused terminals are connected to V_{SS}.

Figure 12. Crosstalk-Control Input to Signal Output

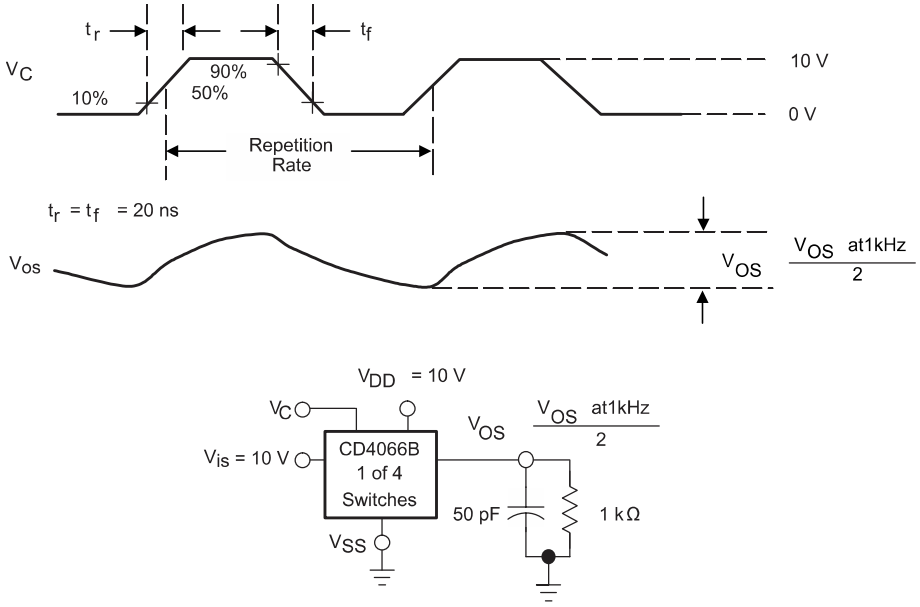
Parameter Measurement Information (continued)



All unused pins are connected to V_{SS}.

Delay is measured at V_{os} level of +10% from ground (turn-on) or on-state output level (turn-off).

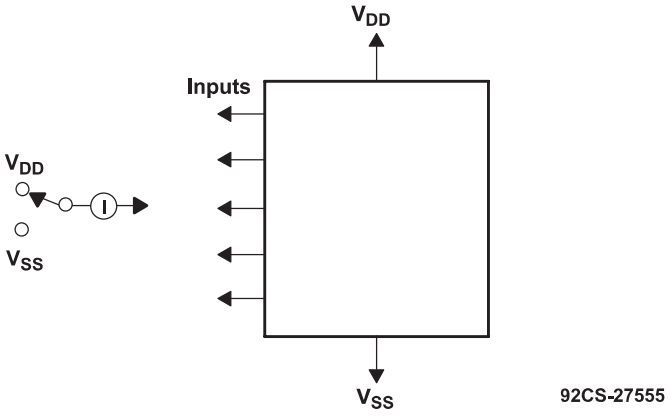
Figure 13. Propagation Delay, t_{PLH}, t_{PHL} Control-Signal Output



All unused pins are connected to V_{SS}.

Figure 14. Maximum Allowable Control-Input Repetition Rate

Parameter Measurement Information (continued)



Measure inputs sequentially to both V_{DD} and V_{SS}. Connect all unused inputs to either V_{DD} or V_{SS}. Measure control inputs only.

Figure 15. Input Leakage-Current Test Circuit

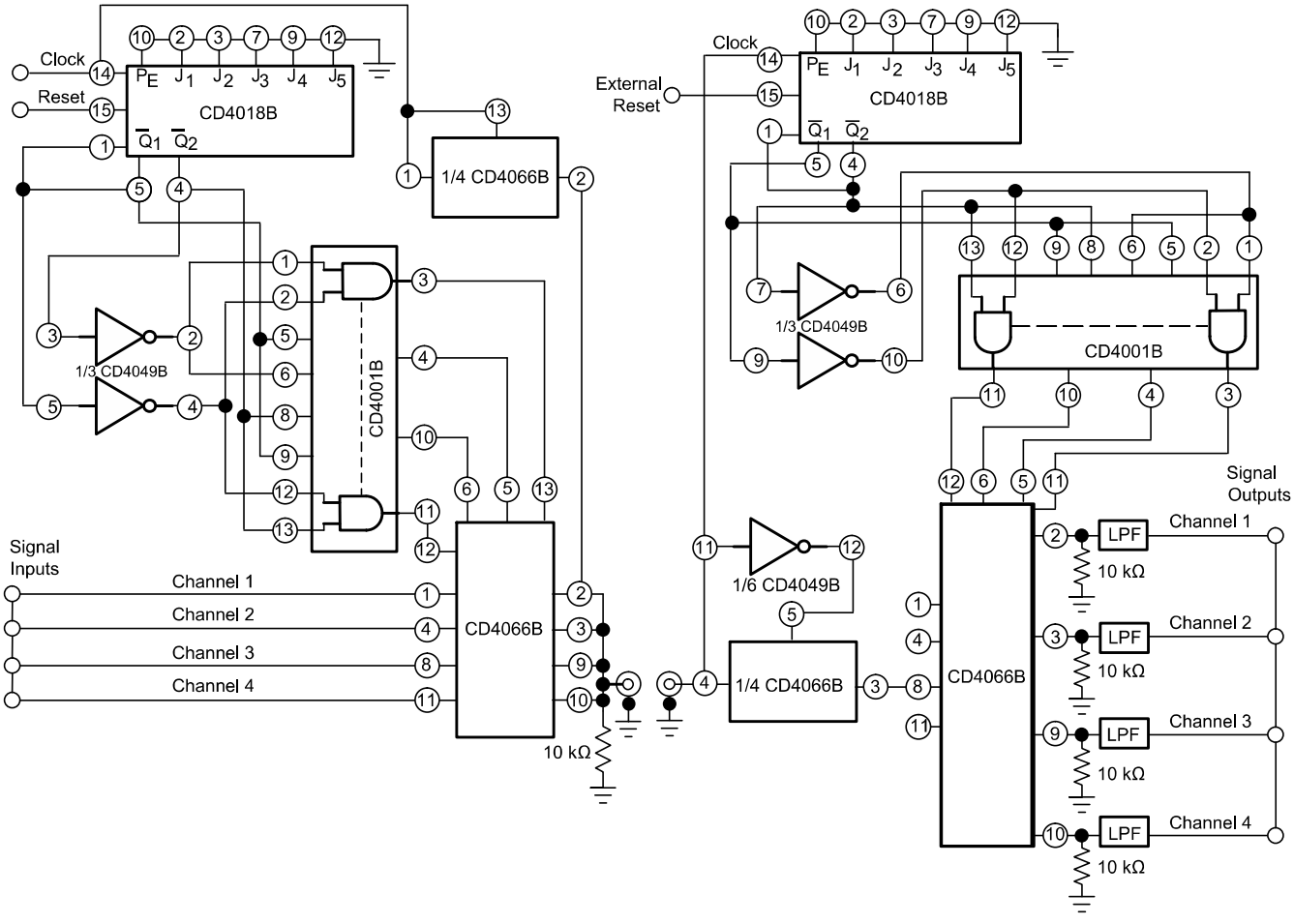


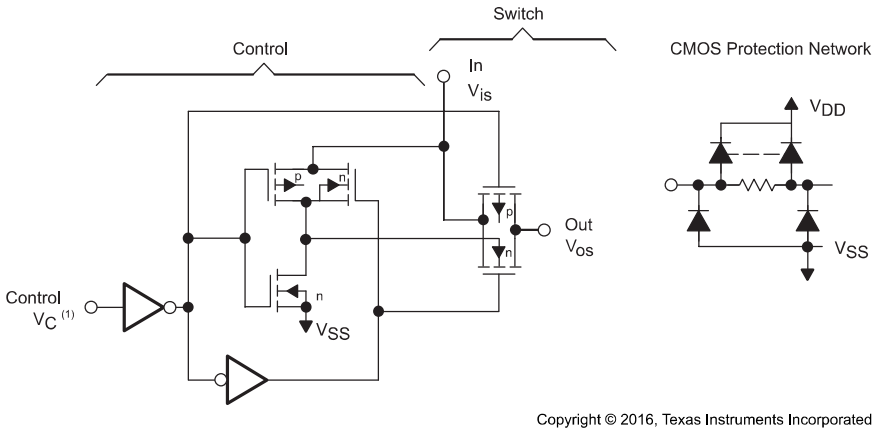
Figure 16. Four-Channel PAM Multiplex System Diagram

8 Detailed Description

8.1 Overview

CD4066B has four independent digitally controlled analog switches with a bias voltage of V_{SS} to allow for different voltage levels to be used for low output. Both the p and the n devices in a given switch are biased on or off simultaneously by the control signal. As shown in Figure 17, the well of the n-channel device on each switch is tied to either the input (when the switch is on) or to V_{SS} (when the switch is off). Thus when the control of the device is low, the output of the switch goes to V_{SS} while when the control is high the output of the device goes to V_{DD}.

8.2 Functional Block Diagram



(1) All control inputs are protected by the CMOS protection network.

(2) All p substrates are connected to V_{DD}.

(3) Normal operation control-line biasing: switch on (logic 1), $V_C = V_{DD}$; switch off (logic 0), $V_C = V_{SS}$.

(4) Signal-level range: $V_{SS} \le V_{is} \le V_{DD}$.

Figure 17. Schematic Diagram of One-of-Four Identical Switches and Associated Control Circuitry

8.3 Feature Description

Each switch has different control pins, which allows for more options for the outputs. Bias Voltage allows the device to output a voltage other than 0 V when the device control is low. The CD4066B has a large absolute maximum voltage for V_{DD} of 20 V.

8.4 Device Functional Modes

Table 1 lists the functions of this device.

Table 1. Function Table

INPUTS		OUTPUT
SIG IN/OUT	CONTROL	SIG OUT/IN
H	H	H
L	H	L
X	L	Hi-Z

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

In applications that employ separate power sources to drive V_{DD} and the signal inputs, the V_{DD} current capability should exceed V_{DD}/R_L (R_L = effective external load of the four CD4066B device bilateral switches). This provision avoids any permanent current flow or clamp action on the V_{DD} supply when power is applied or removed from the CD4066B device.

In certain applications, the external load-resistor current can include both V_{DD} and signal-line components. To avoid drawing V_{DD} current when switch current flows into pins 1, 4, 8, or 11, the voltage drop across the bidirectional switch must not exceed 0.8 V (calculated from r_{on} values shown).

No V_{DD} current flows through R_L if the switch current flows into pins 2, 3, 9, or 10.

9.2 Typical Application

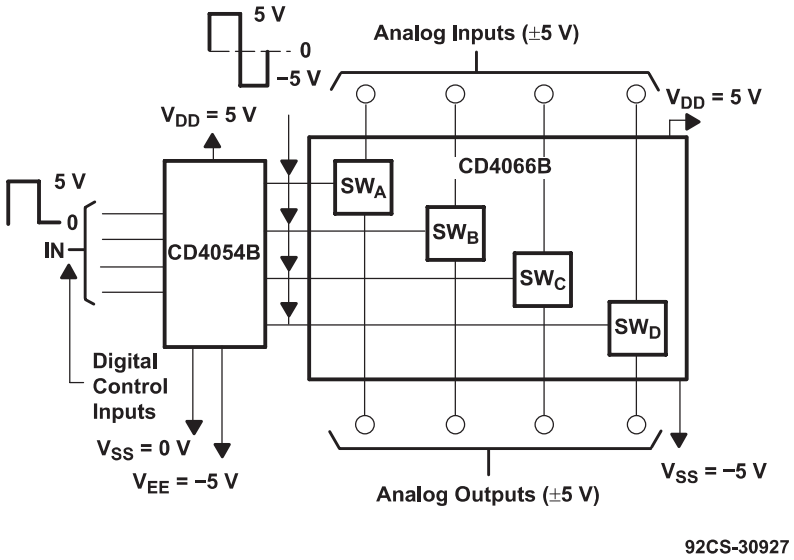


Figure 18. Bidirectional Signal Transmission Through Digital Control Logic

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Avoid bus contention because it can drive currents in excess of maximum limits. The high drive also creates fast edges into light loads, so consider routing and load conditions to prevent ringing.

9.2.2 Detailed Design Procedure

1. Recommended Input Conditions:
   - For rise time and fall time specifications, see $\Delta t/\Delta v$ in *Recommended Operating Conditions*.
   - For specified high and low levels, see V_{IH} and V_{IL} in *Recommended Operating Conditions*.
2. Recommended Output Conditions:
   - Load currents should not exceed ±10 mA.

Typical Application (continued)

9.2.3 Application Curve

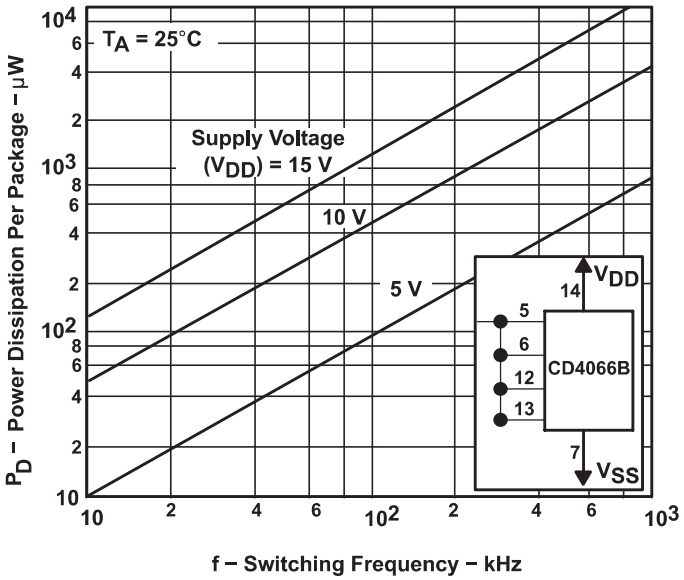


Figure 19. Power Dissipation vs. Switching Frequency

10 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in *Recommended Operating Conditions*.

Each VCC pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1-µF is recommended; if there are multiple VCC pins, then 0.01-µF or 0.022-µF is recommended for each power pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. A 0.1-µF and a 1-µF are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs must never float.

In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they are tied to GND or VCC, whichever makes more sense or is more convenient. It is generally acceptable to float outputs, unless the part is a transceiver. If the transceiver has an output enable pin, it disables the output section of the part when asserted. This does not disable the input section of the I/Os, so they cannot float when disabled.

11.2 Layout Example

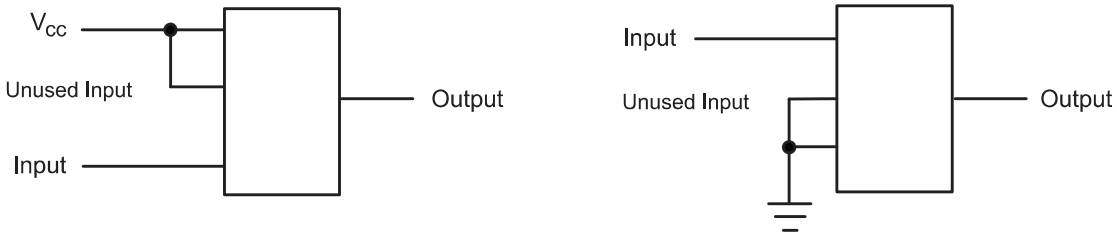


Figure 20. Diagram for Unused Inputs

12 Device and Documentation Support

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.